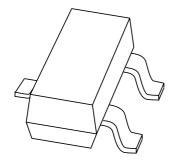
DISCRETE SEMICONDUCTORS

DATA SHEET



BAV74High-speed double diode

Product data sheet Supersedes data of 1999 May 11 2004 Jan 14



High-speed double diode

BAV74

FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 50 V
- Repetitive peak reverse voltage: max. 60 V
- Repetitive peak forward current: max. 450 mA.

APPLICATIONS

• High-speed switching in thick and thin-film circuits.

DESCRIPTION

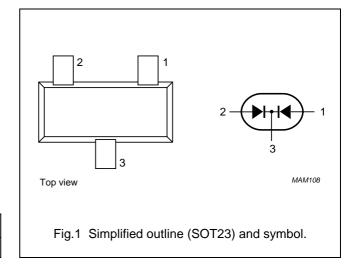
The BAV74 consists of two high-speed switching diodes with common cathodes, fabricated in planar technology, and encapsulated in a small SOT23 plastic SMD package.

MARKING

| TYPE NUMBER | MARKING CODE(1) |
|-------------|-----------------|
| BAV74 | JA* |

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | anode (a1) |
| 2 | anode (a2) |
| 3 | cathode |



Note

- * = p : Made in Hong Kong.
 - * = t : Made in Malaysia.
 - * = W: Made in China.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|---------------------------------|---|------|------|------|
| Per diode | | | | | |
| V _{RRM} | repetitive peak reverse voltage | | _ | 60 | V |
| V _R | continuous reverse voltage | | _ | 50 | V |
| I _F | continuous forward current | single diode loaded; note 1; see Fig.2 | _ | 215 | mA |
| | | double diode loaded; note 1; see Fig.2 | _ | 125 | mA |
| I _{FRM} | repetitive peak forward current | | _ | 450 | mA |
| I _{FSM} | non-repetitive peak forward | square wave; T _j = 25 °C prior to surge; see Fig.4 | | | |
| | current | t = 1 μs | _ | 4 | Α |
| | | t = 1 ms | _ | 1 | Α |
| | | t = 1 s | _ | 0.5 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C; note 1 | _ | 250 | mW |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | _ | 150 | °C |

Note

1. Device mounted on an FR4 printed-circuit board.

High-speed double diode

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ORDERING INFORMATION

| TYPE NUMBER | PACKAGE | | | |
|-------------|-----------------------|--|-------|--|
| TIPE NOMBER | NAME DESCRIPTION VERS | | | |
| BAV74 | _ | plastic surface mounted package; 3 leads | SOT23 | |

ELECTRICAL CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

| SYMBOL | PARAMETER | PARAMETER CONDITIONS | | | |
|-----------------|--------------------------|---|------|----|--|
| Per diode | | | | | |
| V _F | forward voltage | see Fig.3 | | | |
| | | I _F = 1 mA | 715 | mV | |
| | | $I_F = 10 \text{ mA}$ | 855 | mV | |
| | | I _F = 100 mA | 1.0 | V | |
| I _R | reverse current | see Fig.5 | | | |
| | | V _R = 25 V | 30 | nA | |
| | | V _R = 50 V | 0.1 | μΑ | |
| | | V _R = 25 V; T _j = 150 °C | 30 | μΑ | |
| | | V _R = 50 V; T _j = 150 °C | 100 | μΑ | |
| C _d | diode capacitance | f = 1 MHz; V _R = 0; see Fig.6 | 1.5 | pF | |
| t _{rr} | reverse recovery time | when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7 | 4 | ns | |
| V _{fr} | forward recovery voltage | when switched from $I_F = 10$ mA; $t_r = 20$ ns; see Fig.8 | 1.75 | V | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------------------|---|------------|-------|------|
| R _{th(j-tp)} | thermal resistance from junction to tie-point | | 360 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | note 1 | 500 | K/W |

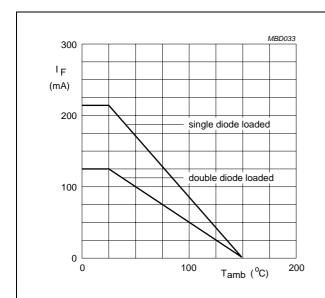
Note

1. Device mounted on an FR4 printed-circuit board.

High-speed double diode

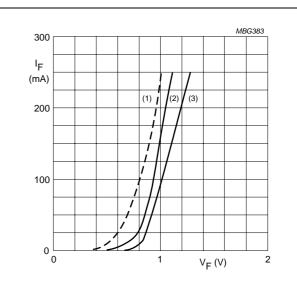
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GRAPHICAL DATA



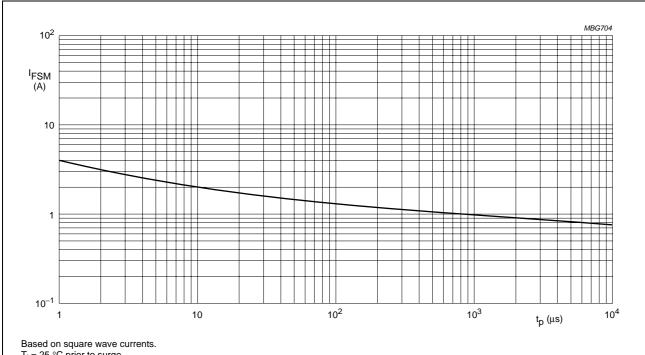
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) T_j = 150 °C; typical values.
- (2) $T_j = 25$ °C; typical values.
- (3) T_j = 25 °C; maximum values.

Fig.3 Forward current as a function of forward voltage.

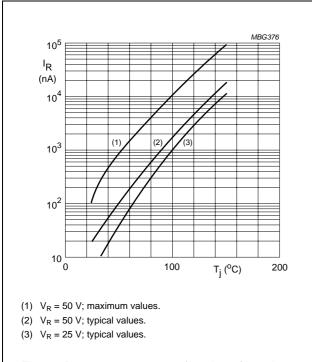


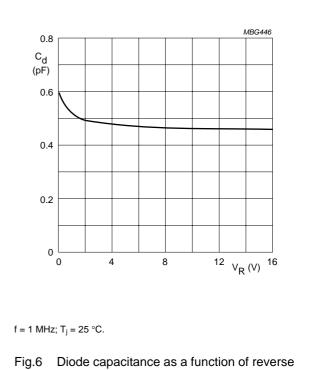
 $T_j = 25$ °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

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voltage; typical values.

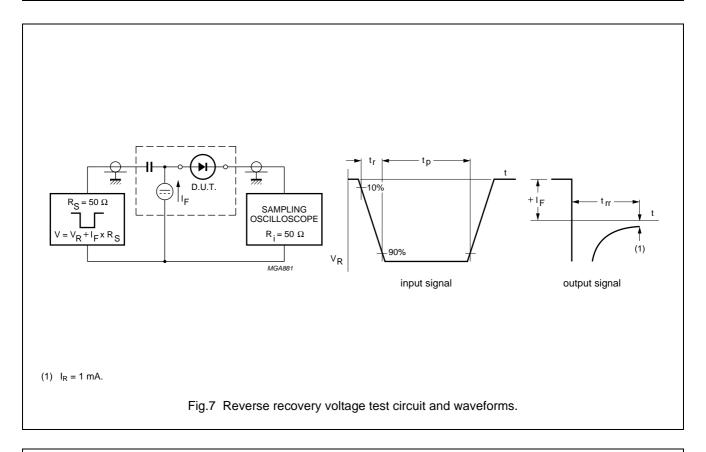
Fig.5 Reverse current as a function of junction temperature.

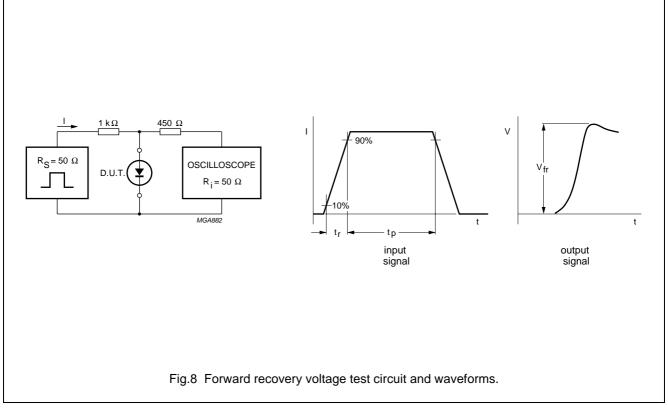
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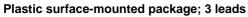




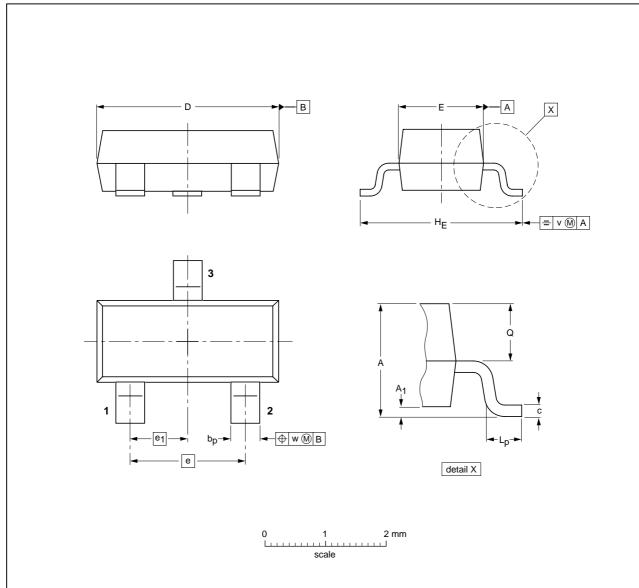
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PACKAGE OUTLINE



SOT23



DIMENSIONS (mm are the original dimensions)

| UNIT | Α | A ₁ max. | bp | С | D | E | е | e ₁ | HE | Lp | Q | v | w |
|------|------------|------------------------|--------------|--------------|------------|------------|-----|----------------|------------|--------------|--------------|-----|-----|
| mm | 1.1 0.9 | 0.1 | 0.48 0.38 | 0.15 0.09 | 3.0 2.8 | 1.4 1.2 | 1.9 | 0.95 | 2.5 2.1 | 0.45 0.15 | 0.55 0.45 | 0.2 | 0.1 |

| OUTLINE | | REFER | EUROPEAN | ISSUE DATE | | |
|---------|-----|----------|----------|------------|------------|----------------------------------|
| VERSION | IEC | JEDEC | JEITA | | PROJECTION | ISSUE DATE |
| SOT23 | | TO-236AB | | | | -04-11-04 06-03-16 |

High-speed double diode

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DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|-----------------------------------|----------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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Printed in The Netherlands R76/04/pp9 Date of release: 2004 Jan 14 Document order number: 9397 750 12392



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